



GPP

2016-10-21

1. 绝对最大额定值

任何情况下都不允许超过的值

Symbol	Parameter	Test Conditions	max	Unit
V_R	DC reverse voltage		600	V
V_{RRM}	Repetitive Reverse Voltage		600	V
$I_{F(AV)}$	Average Forward Current	$T_C=75^\circ\text{C}$, rec,d=0.5	95	A
	RMS Forward	$T_C=75^\circ\text{C}$	142	A



Sym bol	Parame- ter	Test Conditions	max	Unit
I _{FSM}	Non-repeti- tive surge forward current	T _j =45 °C ;t=10ms(50Hz),sine	1200	A
		T _j =45 °C ;t=8.3ms(60Hz),sine	1300	A
		T _j =75 °C ;t=10ms(50Hz),sine	1080	A

Symbol	Function	Value	40 to 100 °C
T _{stg}	Storage Temperature Range	-40 to 125	-40 to 125
T _{op}	Operating Temperature Range	-40 to 125	-40 to 125
P _{tot}	Total Power Dissipation	200	200
V _{ce(sat)}	V _{ce(sat)}	0.2	0.2



°C

器件的额定电压值 应高于实际最大电压值20%

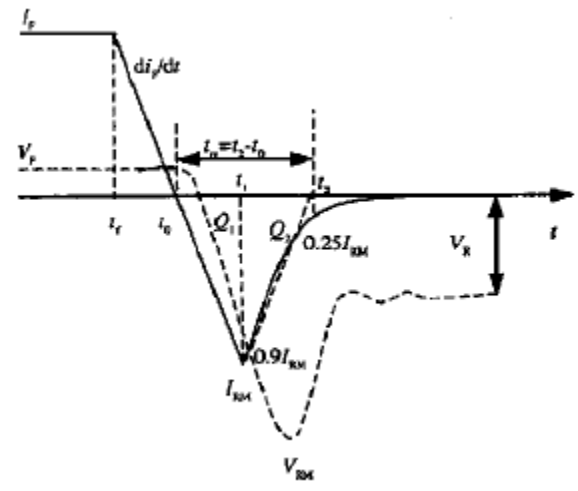
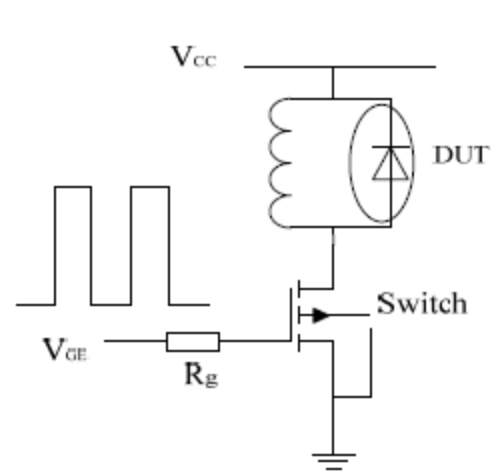
电流值 应高于实际最大
功耗值 应高于实际最大

电流值20%
功耗的50%

150 °C



Sy mb ol	Para- meter	Test Conditions	Mi n.	Typ.	Max .	U nit
t_{rr}	Reverse Recovery Time	$I_F=100$	--	14	--	ns
		A C $V_R=30$	--	250	300	ns
I_{RM}	Max. Reverse Recovery Current	0V $di_F/dt=-200A/\mu s$	--	21	--	A
		$T_J=100^\circ$ C				





Sym bol	Parameter	Min	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance Junction-to-Case	--	--	0.45	K/W

电子元件的难易程度，热阻值越小，散热性能越好。如果使用手册

通常所说的 (1) 沟道 / 封装之间的热阻抗 $R_{th}(ch-C)$

之间的热阻抗 $R_{th}(ch-A)$ (2) 沟道 / 周围环境之

$$R_{th(ch-A)} = \frac{T_{ch(max)} - T_A}{P}$$

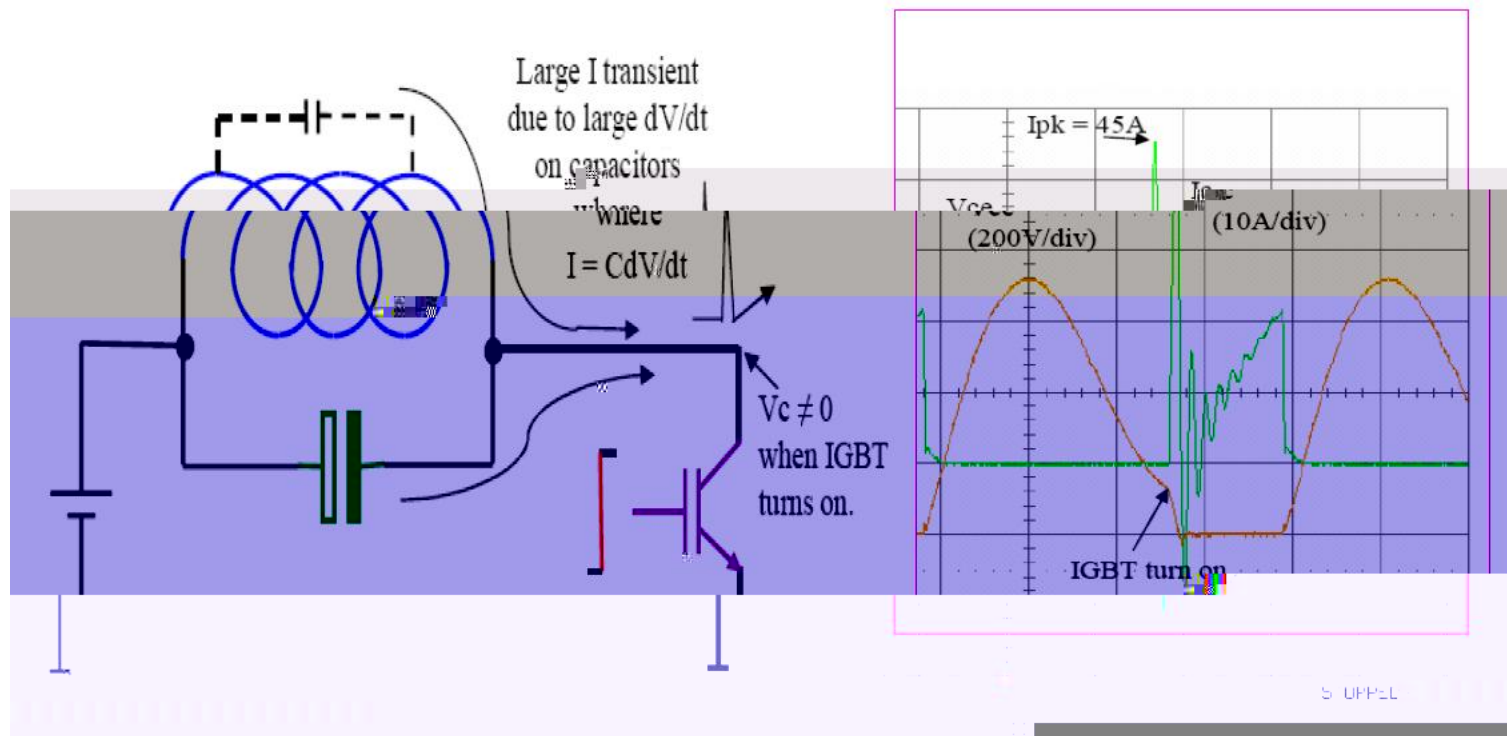
T (TA=25-deg C)



■ Single-end Quasi-resonant converter main circuit



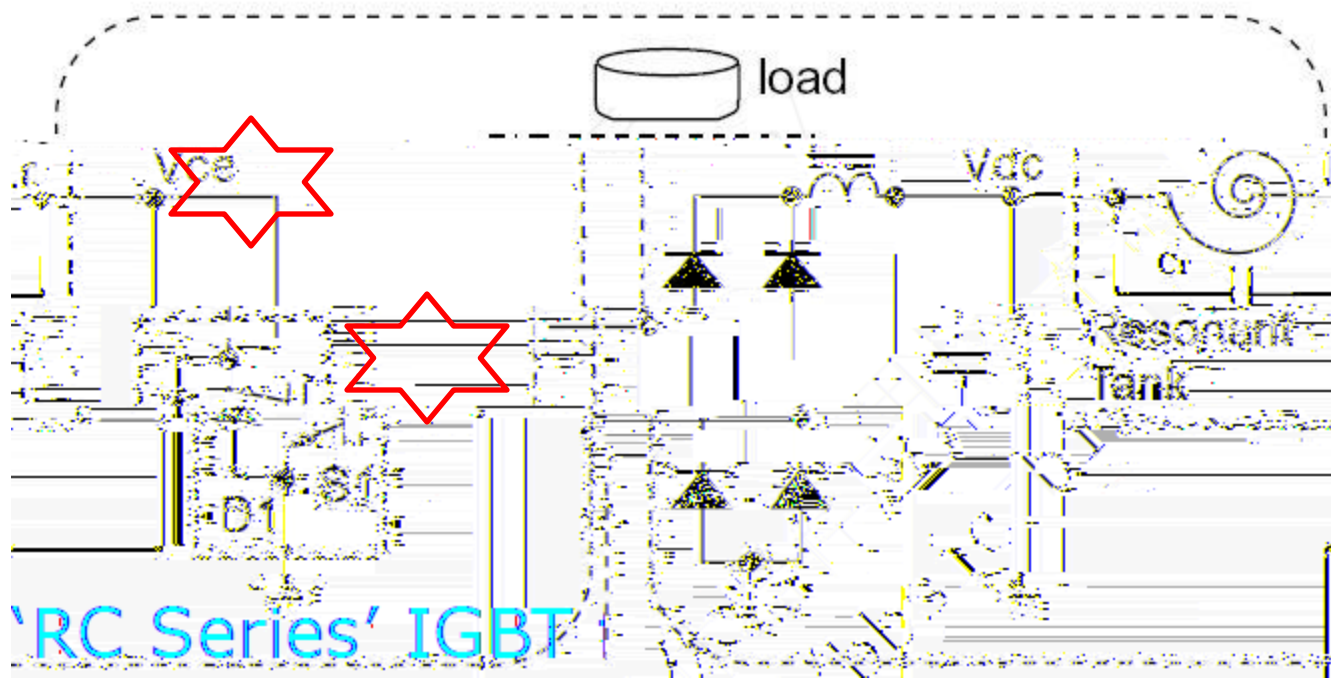
- Quasi-resonant Converter
- Low



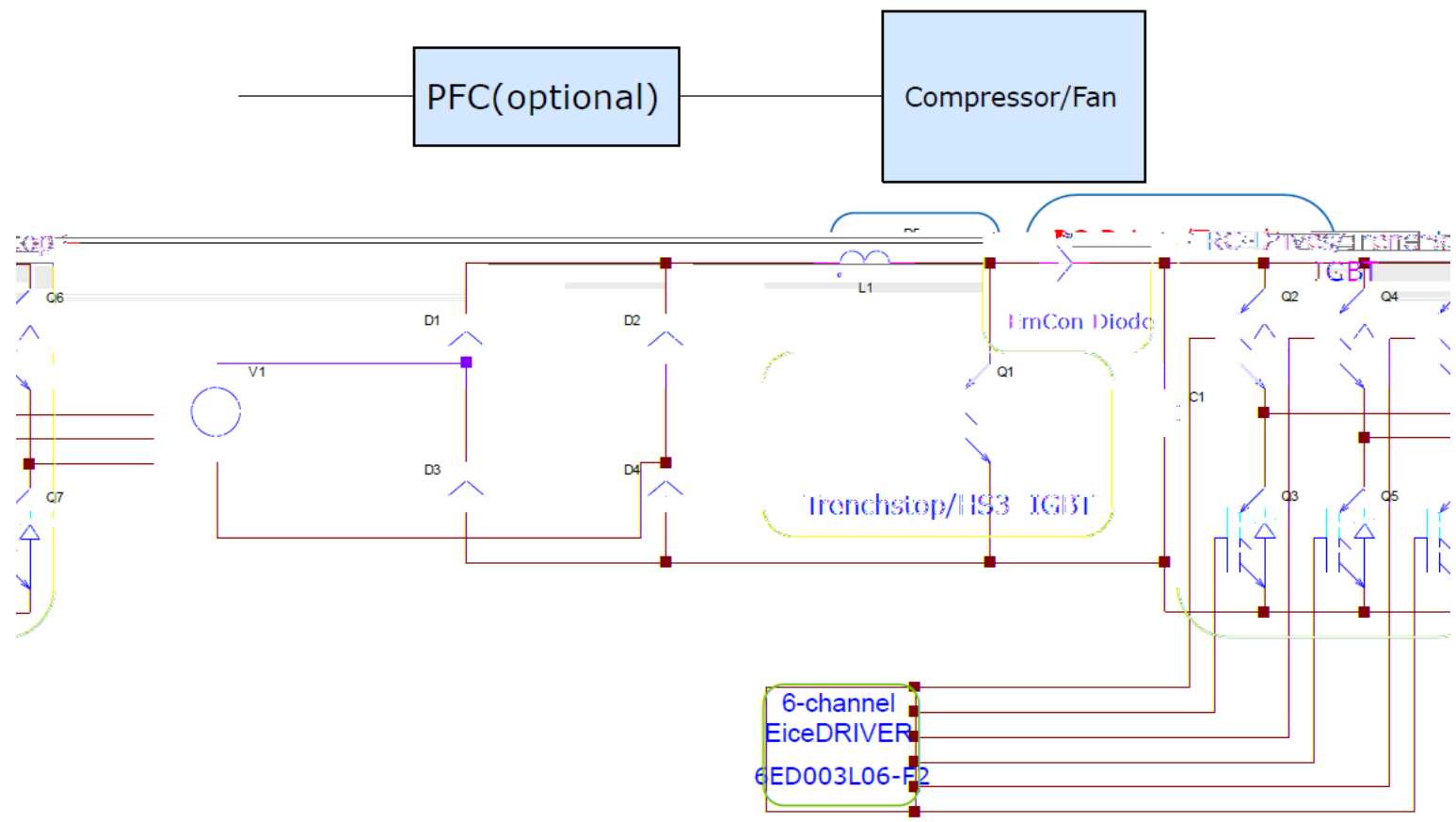
IGBT

$$I = C \frac{dV}{dt}$$

$$V = L \frac{dI}{dt}$$



$$I = C \, dV/dt$$
$$V = L \, dI/dt$$

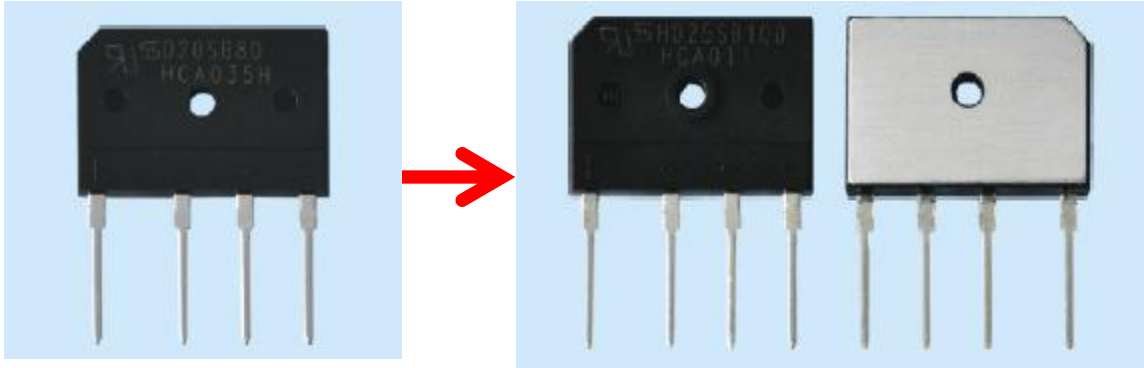




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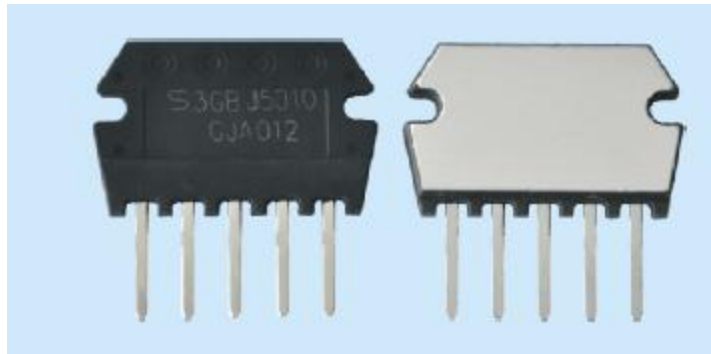
- D15SB80/ D15SB100
- D20SB80/ D20SB100
- D25SB80/ D25SB100
- D35SB80/ D35SB100

HD



2.

- GBJ1510
- GBJ2510





GPP

- 1.
2. :

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- 1.
- 2.
- 3.
- 4.
- 5.



Q & A